## Electric eld inversion asymmetry: Rashba and Stark e ects for holes in resonant tunneling devices

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W e report experim ental evidence of excitonic spin-splitting, in addition to the conventional Zeem an e ect, produced by a combination of the Rashba spin-orbit interaction, Stark shift and charge screening. The electric-eld-induced modulation of the spin-splitting are studied during the charging and discharging processes of p-type G aA s/A IA s double barrier resonant tunneling diodes (RTD) under applied bias and magnetic eld. The abrupt changes in the photolum inescence, with the applied bias, provide inform ation of the charge accumulation e ects on the device.

The e ect of the spin-orbit (SO) interaction in quasitwo-dimensional (Q 2D) systems has attracted renewed attention in recent years. The topic has been on the focus of many optical and transport investigations of spin-related phenom ena in nanoscopic system s [1, 2, 3], a subject of great fundam ental and technological interest [4, 5, 6, 7]. In this letter, we address experimental evidence of electric eld coupling to the spin degree of freedom of carriers in RTD; here in particular, the prevailing in uence can be attributed to the SO and Stark effects on the hole electronic structure. These interactions are relevant to the study of the internal electric elds and the charge accumulation in the structure. The simultaneous investigation of optical and transport properties at high magnetic and electric parallel elds, has permitted a thorough characterization of the main processes involved in the system response. The novelty of this result consists of the optical detection of electric eld modulation of the e ective spin-splitting beyond the Zeem an e ect and its unambiguous correlation to the transport mechanism swhich is responsible for the charge buildup in the states of the RTD.

This study is carried out on a symmetric p i p G aA s=A lA s RTD, that has been previously used to characterize hole space charge buildup and resonant e ects in a magnetic eld §]. The structure is in the form of a 400 m diam eterm esa with a metallic A uG e annular top contact to allow optical access. The diode was mounted in a superconducting magnet and the emission spectra were recorded using a double spectrom eter coupled to a CCD system with polarizer facilities to select left (right)  $^{+(-)}$  con gurations. When light from an Ar<sup>‡</sup> laser is focused close to the surface, minority electrons are created [8]. As the bias approaches a resonant condition,

the carrier density inside the QW increases and then decreases, resulting in the negative di erential resistance (NDR) region when the resonance is traversed. The photo-generated electrons tunneling into the QW layer can recombine with the injected holes or tunnel out of the well layer. These processes are represented schem atically in the Fig.1 (a).

The I V characteristics, shown in Fig.1 (b), displays a series of peaks associated with the injected holes  $(I_{dark})$  from the hole accumulation layer formed in the outside interface of the diode (see Fig. 1 (a)). Under illumination, an increase of current is observed  $(I_{light})$  due to the injection of minority electrons. Under this condition, is noted the emergence of polarized photolum inescence (PL) emissions from electron-hole (e-h) pair recombinations inside the QW layer, as shown schematically in the top panel. These PL spectra were recorded for + and

polarizations as a function of the bias. The energy of the PL peaks as well as the resulting spin-splitting as a function of bias are shown in Figs. 1 (c) and (d), respectively. We now focus on the mechanism s responsible for the abrupt changes detected at the critical voltages, m arked with dashed-lines, in Fig. 1. A s the bias (electric

eld) increases, both PL polarized peak energies show the expected red-shift induced by the quantum Stark e ect, but also the sharp discontinuities at the hole-resonant voltages. The abrupt variation of the PL-peak energies has been attributed to changes in the QW level charge density near the critical voltages; thus inducing changes on the built-in electric eld  $\Im$ . These discontinuities are m ore evident in the total spin-splitting energy vs bias, shown in Fig.1 (d).

Fig. 1 (d) shows uctuations of the spin-splitting energy and an increasing trend as bias is swept between

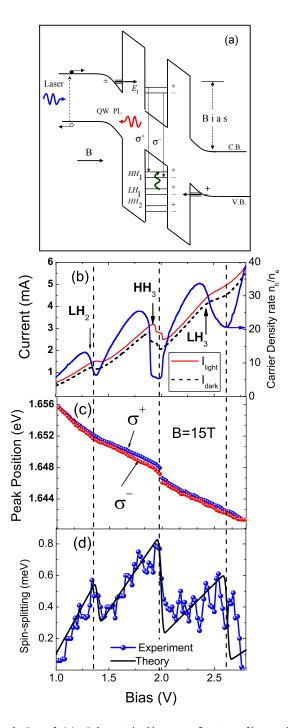


FIG.1: Panel (a): Schem atic diagram s for tunneling and recombination processes in the G aAs AlAs RTD with 4.2nm (5.1nm) well (barriers) width, under illum ination. Below panels: Vertical dashed-lines show the critical voltages where abrupt changes in the properties occur for B = 15 T. Panel (b): The I V characteristics with ( $I_{light}$ ) and without ( $I_{dark}$ ) illum ination. The carrier density rate calculated through Eq. (3). Panel (c): Energy peak positions of PL spectra as a function of bias. Panel (d) Sym bols: m easured spin-splitting of excitonic recombinations, for increasing bias. Solid-line: C alculated spin-splitting generated by SO e ects, in addition to the conventional Zeem an e ect.

two hole critical voltages. The sharp decrease occurs when the NDR region is crossed and the QW level is being discharged. Besides the usual Zeem an e ect, other two SO interactions modify the e ective spin-splitting: (i) the bulk inversion asymmetry (BIA or Dresselhaus SO) induces spin-splitting only in zincblende heterostructures, (ii) the structure inversion asymmetry (SIA or Rashba SO) causes spin-splitting under applied electric eld [0, 11]. Both contributions depend on the material SO parameters and their e ects can be enhanced by the presence of a magnetic eld [0]. The properties addressed in this work occur at high electric eld (bias), then the Rashba SO contribution becom es dom inant and we will not consider the BIA SO term.

The complex behavior of our device is studied by modeling the states by a square potential with a bias dependent electric eld due to the charge density built in the QW levels. The coupling between this e ective electric eld and the spin degree of freedom is introduced via the Rashba SO Ham iltonian for electrons [10, 11] and for holes [12]. The kinetic Luttinger Ham iltonian provides an accurate description of the valence band admixture and perm its to treat m agnetic (B) and electric (F) elds, aswellastheRashbaSO in the same framework.The full Ham iltonian, H <sup>cond=val</sup> = H <sup>L</sup>  $J_{j+1} = Fz + \hat{H}^{\circ}$ , may be decomposed into three terms: (i) H  $^{\rm L}$  that describes the dynam ics associated with the Landau and Zeem an quantization in a magnetic eld, (ii)  $\mathbf{L}_{j+1}$ eF z contains all Stark shift-related terms that produce the inversion asymmetry induced by the electric eld (F); here  $J_{j+1}$ is the (2j+1)-rank unity matrix, and (iii) the Rashba SO term that couples the dynam ical linear momentum with the spin degree of freedom. The SO term is treated in the (2j+1)-rank representation of the totalm om entum with j = 1=2 for electrons and j = 3=2 for holes [12] as

$$H^{SO} = \frac{P_{\overline{2F}}}{c} i aJ_{+} a^{Y}J : \qquad (1)$$

Here  $_{cond (val)}$  is the Rashba SO parameter for conduction (valence) band,  $_{c}$  is the magnetic cyclotron radius, and  $J = \frac{1}{2} (J_{x} \quad J_{y})$ , where  $J_{i}$  is the 4 4 (2 2) angular momentum matrix for holes (electrons). One advantage of this SO representation is that it permits a wavefunction expansion in each component of the spinor state with the required symmetries de ned by the lateral and vertical con nem ent types. The basis set also combines the band edge periodic B loch functions in the totalm omentum representation:  $j_{s}$  "#i,  $j_{h}$  "#i,  $j_{h}$  "#i, the vertical eigenstates:  $A_{2k-1}(z)$ -even and  $A_{2k}(z)$ -odd parity for k = 1; 2; ...; and the lateral Landau states N i. The eigenfunctions for the conduction (  $_{c}$ ) and for the

valence band states (  $_{\rm v}$  ) have the general form ,

$$c = \begin{cases} 2 & 3 \\ A_{1}^{c} N i j s "i \\ 6 & A_{1}^{c} N + 1 i j s #i ? \\ A_{2}^{c} N i j s "i \\ A_{3}^{c} ::: \end{cases}$$

$$c = \begin{cases} 2 & A_{1}^{v} N & 2 i j h "i \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{2}^{v} N & 1 i j h "i ? \\ A_{3}^{v} ::: \end{cases}$$

$$c = \begin{cases} 2 & A_{1}^{v} N & 2 i j h "i ? \\ A_{1}^{v} N & 1 i j h "i ? \\ A_{2}^{v} N & 1 i j h "i ? \\ A_{2}^{v} N & 1 i j h "i ? \\ A_{2}^{v} N & 1 i j h "i ? \\ A_{2}^{v} N & 1 i j h "i ? \\ A_{2}^{v} N & 1 i j h #i ? \\ A_{2}^{v} N & 1 i j h #i ? \\ A_{2}^{v} N & 1 i j h #i ? \\ A_{3}^{v} ::: \end{cases}$$

$$(2)$$

Note that N = 1;0;1;2;::: is an elective Landau index labeling the lateral con nem ent symmetries (parities) of each component. The sequence of periodic valence B loch states in the components is determined by the sequence chosen to write the Luttinger H am iltonian. These vector states have, in principle, in nite dimension since the index k, used to enumerate the vertical functions  $A_{2k-1}$ and  $A_{2k}$ , runs over all positive integer numbers.

Fig. 2 (a) shows the calculated electron and hole m aqnetic dispersions for the lowest energy subband of carriers in the conduction (E  $_1$ ) and in the valence (H H  $_1$ ,  $LH_1$ ) bands of the GaAs QW. Note that the e ective Zeem an splitting for holes and electrons can be tuned by the external elds F and B. This also re ects the strong adm ixture of states generated by the com bination of Rashba SO plus Stark e ects, in particular, for the valence band where the strong nonparabolicity is present in the kinetic Luttinger Hamiltonian. A comparison between the contribution from the nonparabolicity (F = 0)and from SO plus Stark e ects (F = 100 kV/cm) to the e ective spin-splitting of the  $H H_1$  ground state, is shown in Fig. 2 (b) for di erent degrees of vertical connement. For xed B-value, an increase of well width increases the energy splitting since the coupling between states with close energy is enhanced. The corresponding interband transition energies, calculated for a  ${\tt G}$  aA s  ${\tt Q}\,{\tt W}$  , are displayed in Fig. 2 (c) as a function of the electric

eld. The inversion asymmetry, introduced by the electric eld, electric eld, electric and vertical symmetries. This coupling leads to the spin-splitting modulation by the electric eld, which is the main topic addressed. Note that the strength of modulation can be enhanced for materials with larger SO parameters as shown in Fig. 2 (d). The larger is the Rashba SO parameter, such as in InAs or InSb, the stronger is the coupling between the electric eld and the spin-degree of freedom.

Superim posed to the external electric eld (bias), there is an internal eld component due to the charge distribution throughout the diode structure. The relation between the applied bias and the total electric eld F experienced by the carriers would require a selfconsistent calculation. Here we consider an average electric eld which qualitatively accounts for the main elects of

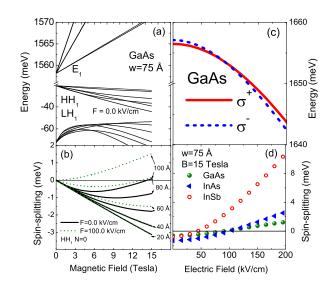


FIG.2: Panel (a): Landau level fan charts (N = 0;1;2) for the rst electron ( $E_1$ ) and hole ( $H H_1$ ,  $LH_1$ ) subbands in a GaAs QW with width w = 75A and F = 0. Panel (b): Calculated Zeem an splitting of the  $H H_1$  ground state. The solid-lines (dashed-lines) indicate the results without (with) the inversion asymmetry induced by the electric eld. Panel (c): Interband transition energies for polarized light em issions in a GaAs QW, with B = 15 Tesla. Panel (d): The additionalSO contribution to the calculated spin-splitting energy of excitonic recombination in identicalQW 's of di erent III-V com pounds, as a function of the electric eld.

the inversion asym m etry on the spin-splitting energy seen in the PL em issions. From I  $\,$  V characteristics with and without illum ination [see Fig.1 (a)] we may estimate the ratio between the majority  $(n_{\rm h})$  and m inority  $(n_{\rm e})$  carrier densities inside the QW , as

$$\frac{n_{h}}{n_{e}} = 2 \frac{I_{dark} (V)}{I_{light} (V) I_{lark} (V)}; \qquad (3)$$

Together with the I V characteristics, this ratio is shown in panel (b) of Fig. 1, as a function of bias and for the highest laser excitation power. Note that in our experimental conditions the density of holes (majority) is always larger than the density of electrons (minority). Moreover,  $n_h = n_e$  increases smoothly during the charge buildup process, as the bias is being swept between two hole resonant voltages and an abrupt drop occurs during the QW discharge (NDR region).

Owing to the smooth variation of  $n_h = n_e$  and to the experimental condition  $n_h = n_e$ , we have chosen to use a total eld F changing linearly with an elective charge density,  $n_h^{eff}$ , and giving rise to an uniform eld. In the presence of an asymmetry induced by the external

eld, this is a fair approximation [3, 14, 15], and can be written

$$F = F^{\text{ext}} + \frac{e}{n_h^{\text{eff}}}; \qquad (4)$$

where = 13:18 is the static dielectric constant for G aAs. A llthe other parameters for G aAs used in the simulation, such as elective masses, Luttinger and R ashba parameters were taken from the literature.

Based on these assumptions we have estimated the asymmetry e ects on the modulation of spin-splitting seen in the PL emissions, due to the charge accumulation in the QW levels. This is compared with experimental results in Fig. 1 (d). A percentage of the experimental wiggly increase is due to charge uctuations on system. Our theoretical model does not take into account any type of charge uctuations.

For this Q 2D hole-rich gas, the P L em issions must arise from the recombination of either positive trions (X  $^+$  ) or neutral excitons  $(X^{0})$  [16, 17]. In order to understand the behavior of the PL peaks in Fig. 1 (c) with abrupt variations at resonant transitions for both spin-up and spin-down recombinations, we must consider the charge density-dependent screening on the binding energy of the excitonic complexes involved in the PL emissions [18]. An increase in the Q 2D carrier density leads to screening of the Coulomb interaction that inevitably weakens the binding energy of the excitonic com plexes [18]. Moreover, the charge buildup also gives rise to modulations to: (i) the e-h Coulomb interaction and; (ii) the Stark shift. Cases (i) and (ii) give opposite contributions to the optical transition energies. Near the critical voltages, case (ii) produces a blue-shift due to the reduction of the e ective electric eld, whereas case (i) induces a red-shift due to the decrease of the excitonic binding energies. These competing e ects give origin to the abrupt changes in the peak position of + and PL em issions of Fig. 1 (c). Therefore, the spin-splitting energy is not a ected by these excitonic corrections.

As nalcomments, the good agreement with experimental increasing trend required an e ective density in  $10 \, {\rm cm}^2 < n_{\rm h}^{\rm eff} < 14$ the range 6  $1^{10}$  cm  $^{2}$ . This is larger than the values reported in Ref. [8] using a different relation between bias and local elds. The larger value for the e ective hole charge density is due to the neglected contribution coming from the hole density in interface accumulation layer. Furtherm ore, the e ective QW width w = 75A was adjusted to the e h pair recombination energy at F = 0. In this p i p sample, the modulation of the excitonic spin-splitting is strongly related to valence band adm ixture. As noted in Fig. 2 (a), the set of H H  $_1$  and L H  $_1$  Landau dispersions are highly nonparabolic, in contrast to the alm ost parabolic conduction band levels. This e ect is strongly a ected by the QW width that determines the separation between the coupled H H $_1$  and L H $_1$  subbands, as shown in Fig.2 (b).

In sum mary, we have observed that spin-splitting dependence on bias is mainly in uenced by the renormalization of the hole charge density in the uniform eld approximation. This spin-splitting induced by the combined e ects of Rashba SO interaction, Stark e ect, Zeem an and interband couplings acts as a probe of the relation between the uctuating internal eld F and the continuously varying bias V. We have shown how the electronic structure is a ected by the modil cation of the e ective eld F in our RTD and by the modulation of the Rashba SO and screening e ects induced by charge uctuations. We have studied these e ects in simultaneous optical and transport m easurements of the main physical processes involved.

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